

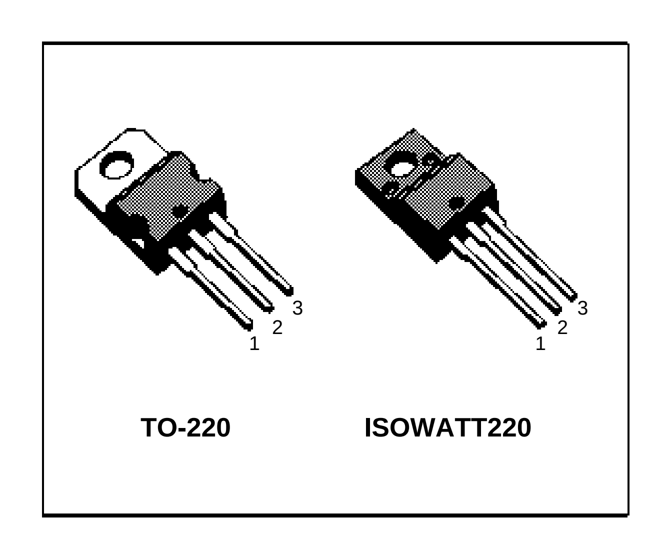
IRF840/FI
IRF841/FI

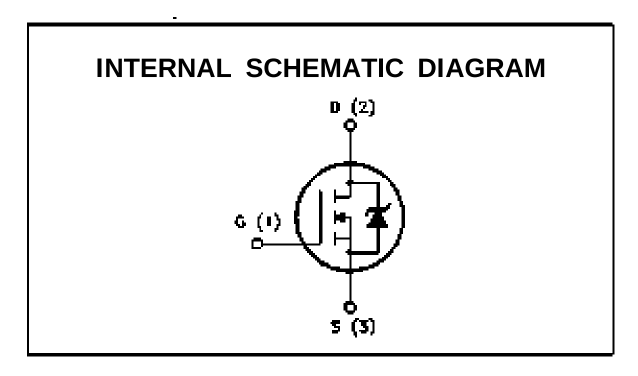
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTORS

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
IRF840	500 V	< 0.85 Ω	8 A
IRF840FI	500 V	< 0.85 Ω	4.5 A
IRF841	450 V	< 0.85 Ω	8 A
IRF841FI	450 V	< 0.85 Ω	4.5 A

- TYPICAL $R_{DS(on)}$ = 0.74 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100^{o}C

APPLICATIONS
- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CHOPPER REGULATORS, CONVERTERS, MOTOR CONTROL, LIGHTING FOR INDUSTRIAL AND CONSUMER ENVIRONMENT





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value				Unit
		IRF				
		840	841	840FI	841FI	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	500	450	500	450	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	500	450	500	450	V
V_{GS}	Gate-source Voltage	± 20				V
I_D	Drain Current (cont.) at T_c = 25 ^{o}C	8	8	4.5	4.5	A
I_D	Drain Current (cont.) at T_c = 100 ^{o}C	5.1	5.1	2.8	2.8	A
I_{DM}(•)	Drain Current (pulsed)	32	32	32	32	A
P_{tot}	Total Dissipation at T_c = 25 ^{o}C	125		40		W
	Derating Factor	1		0.32		W/^{o}C
V_{ISO}	Insulation Withstand Voltage (DC)	—		2000		
T_{stg}	Storage Temperature	-65 to 150				^{o}C
T_j	Max. Operating Junction Temperature	150				^{o}C

(•) Pulse width limited by safe operating area

THERMAL DATA

		TO-220	ISOWATT220	
$R_{thj-case}$	Thermal Resistance Junction-case Max	1	3.12	$^oC/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient Max	62.5		$^oC/W$
R_{thc-s}	Thermal Resistance Case-sink Typ	0.5		$^oC/W$
T_l	Maximum Lead Temperature For Soldering Purpose	300		^oC

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	8	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25\ ^oC$, $I_D = I_{AR}$, $V_{DD} = 25$ V)	510	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$)	13	mJ
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive ($T_c = 100\ ^oC$, pulse width limited by T_j max, $\delta < 1\%$)	5.1	A

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\ ^oC$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\ \mu A$ $V_{GS} = 0$ for **IRF840/840FI** for **IRF841/841FI**	 500 450			 V V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	V_{DS} = Max Rating V_{DS} = Max Rating x 0.8 $T_c = 125\ ^oC$			250 1000	µA µA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20$ V			± 100	nA

ON (∗)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\ \mu A$	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V$ $I_D = 4.4$ A		0.74	0.85	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10$ V	8			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (∗)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 4.4$ A	4.9	6		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25$ V f = 1 MHz $V_{GS} = 0$		1100 190 80	1500 240 110	pF pF pF



ELECTRICAL CHARACTERISTICS (continued)

SWITCHING RESISTIVE LOAD

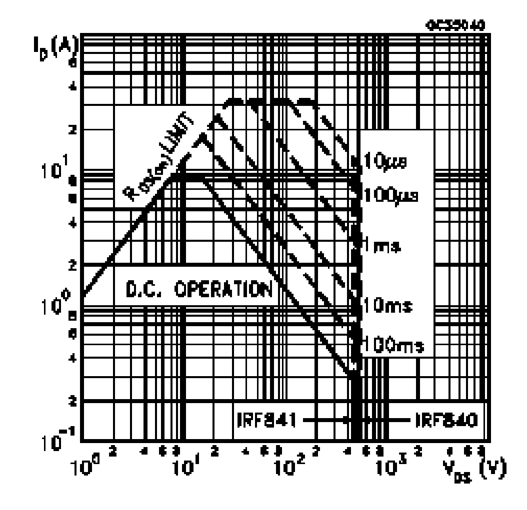
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on Time Rise Time Turn-off Delay Time Fall Time	V_{DD} = 200 V I_D = 4 A R_i = 4.7 Ω (see test circuit)		40 35 80 20	50 43 100 25	ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	I_D = 8 A V_{GS} = 10 V V_{DD} = Max Rating x 0.8 (see test circuit)		75 9 39	95	nC nC nC

SOURCE DRAIN DIODE

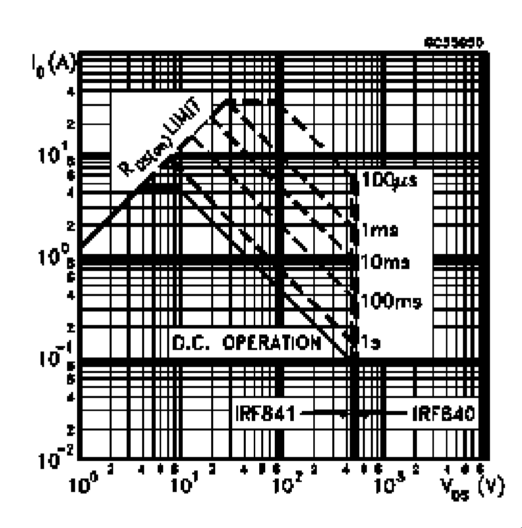
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				8 32	A A
V_{SD} (∗)	Forward On Voltage	I_{SD} = 8 A V_{GS} = 0			2	V
t_{rr} Q_{rr}	Reverse Recovery Time Reverse Recovery Charge	I_{SD} = 8 A di/dt = 100 A/µs V_{DD} = 100 V T_j = 150 °C		700 12		ns µC

(∗) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %
(•) Pulse width limited by safe operating area

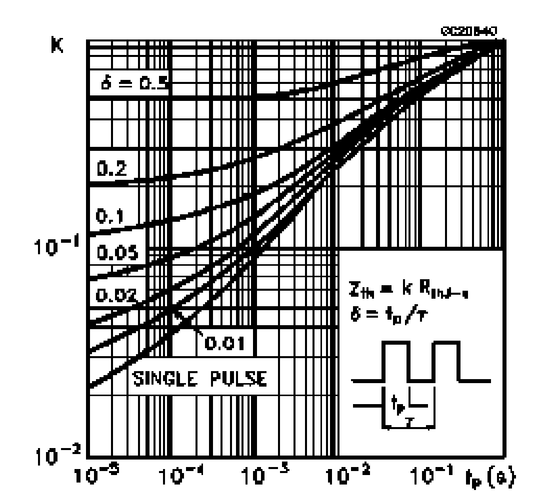
Safe Operating Area for TO-220



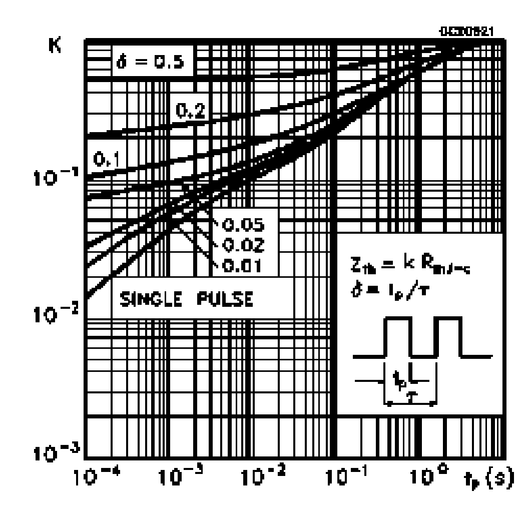
Safe Operating Area for ISOWATT220



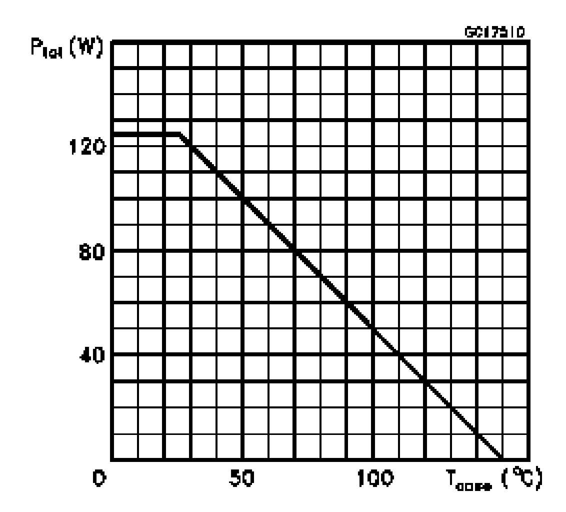
Thermal Impedance for TO-220



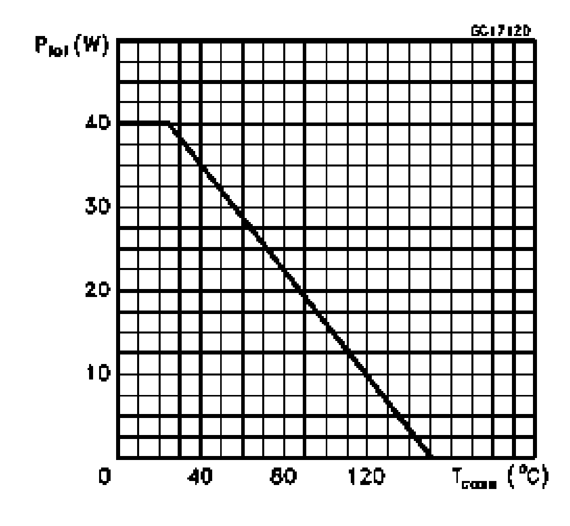
Thermal Impedance for ISOWATT220



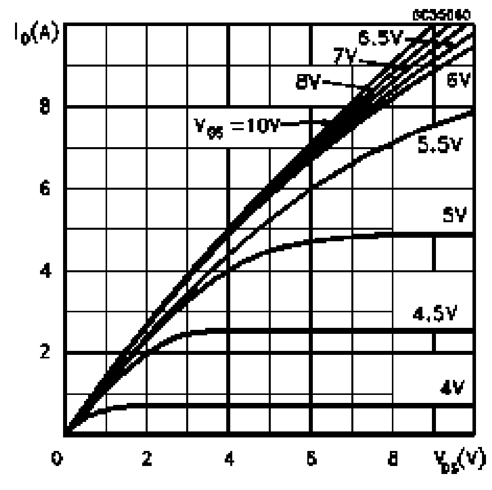
Derating Curve for TO-220



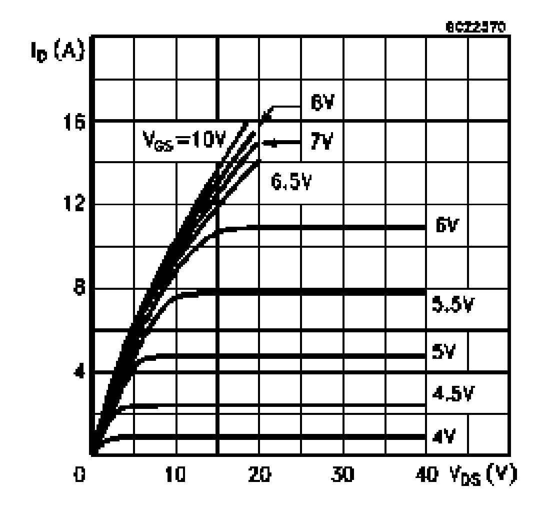
Derating Curve for ISOWATT220



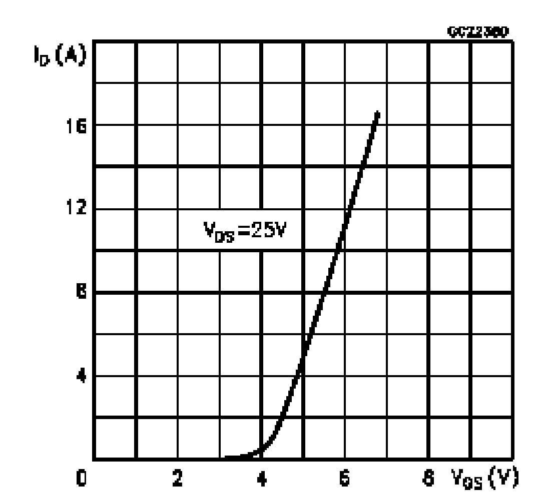
Output Characteristics



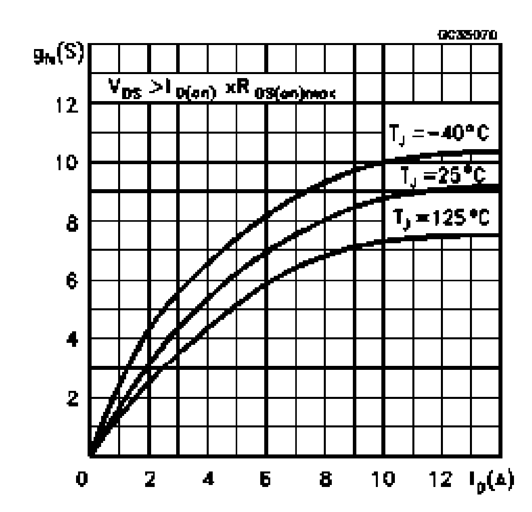
Output Characteristics



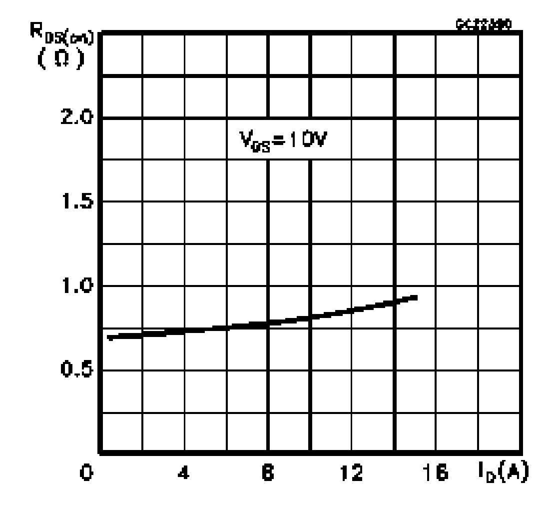
Transfer Characteristics



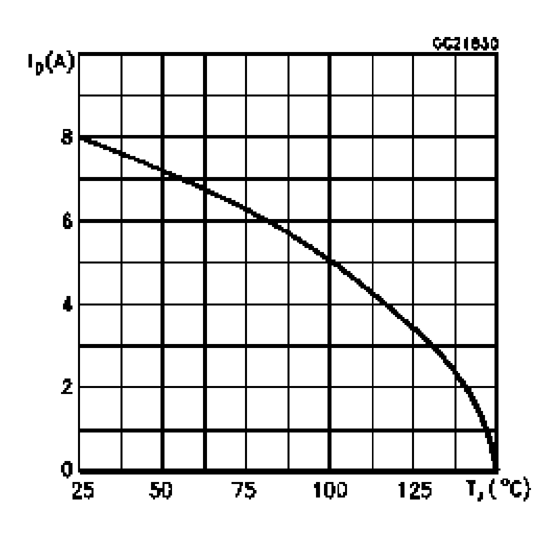
Transconductance



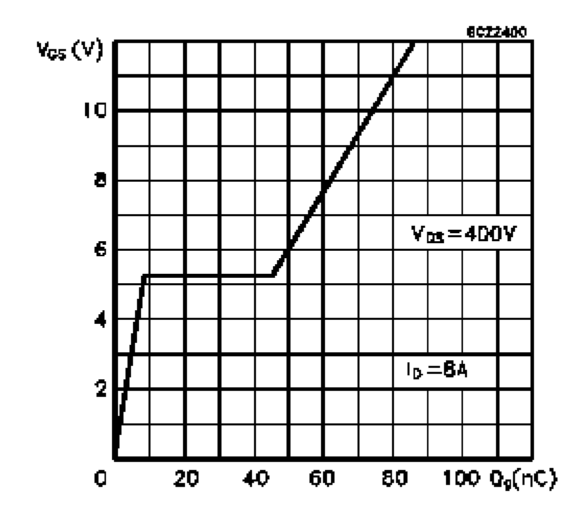
Static Drain-source On Resistance



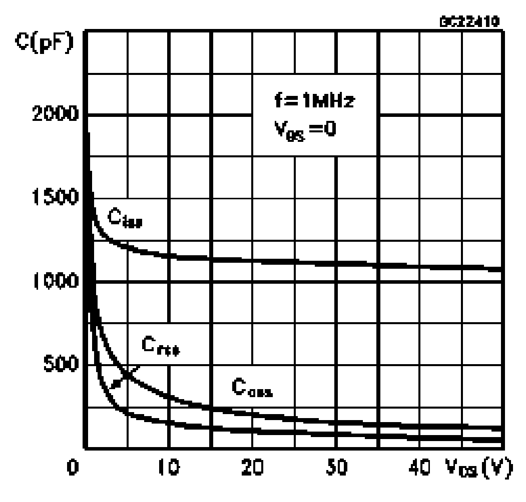
Maximum Drain Current vs Temperature



Gate Charge vs Gate-source Voltage

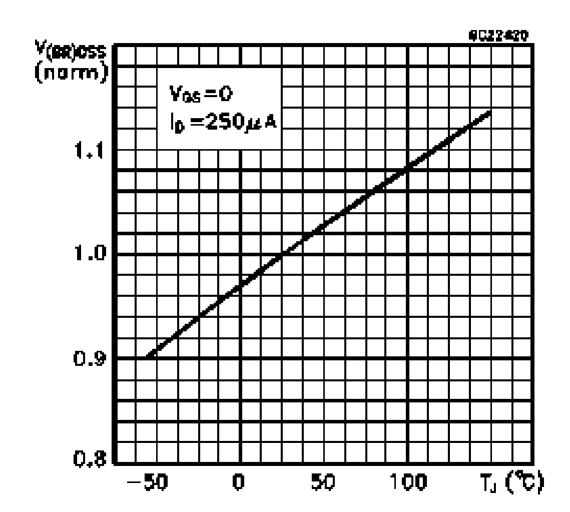


Capacitance Variations

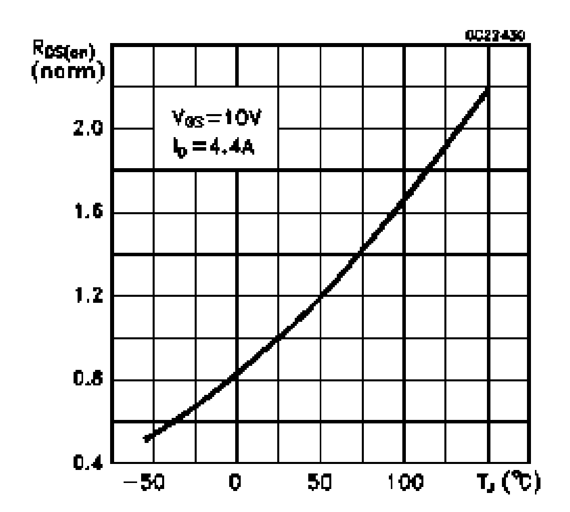




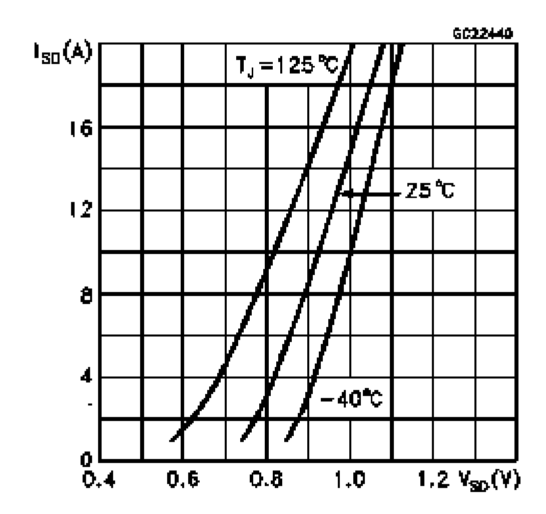
Normalized Breakdown Voltage vs Temperature



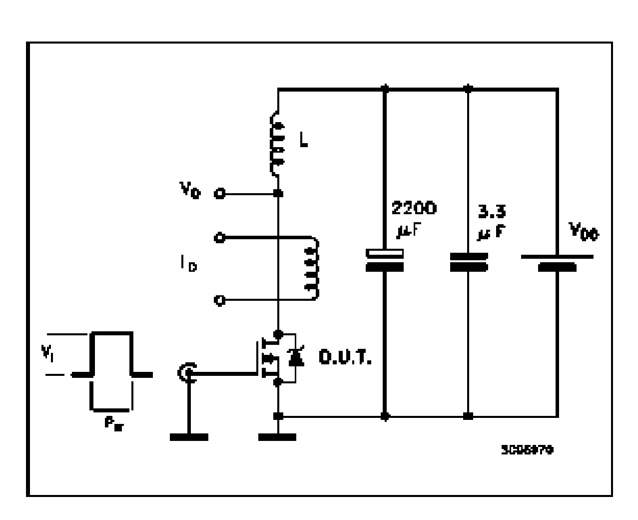
Normalized On Resistance vs Temperature



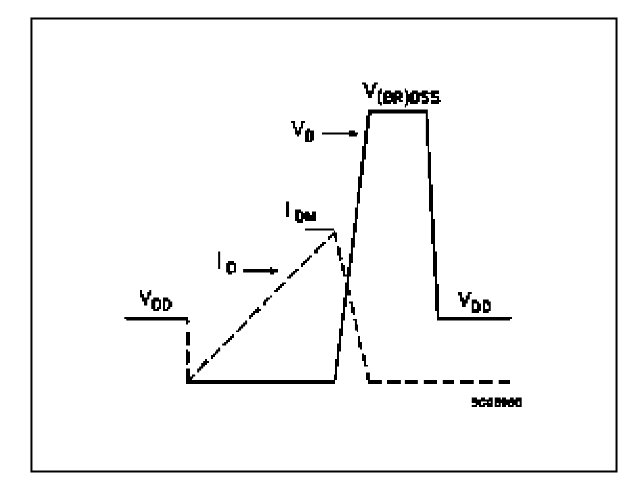
Source-drain Diode Forward Characteristics



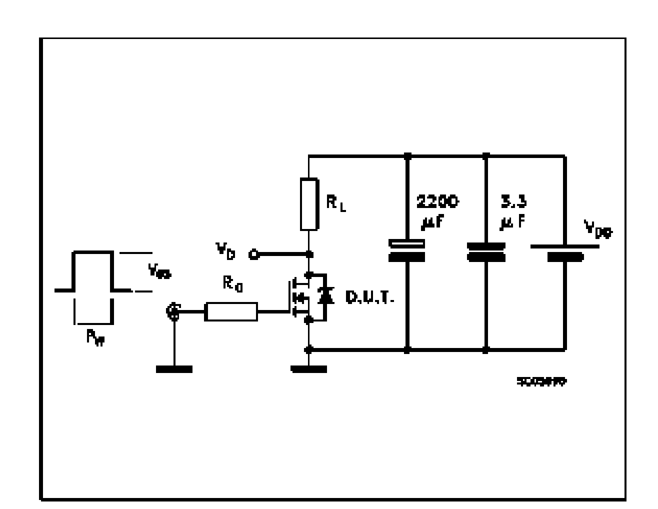
Unclamped Inductive Load Test Circuit



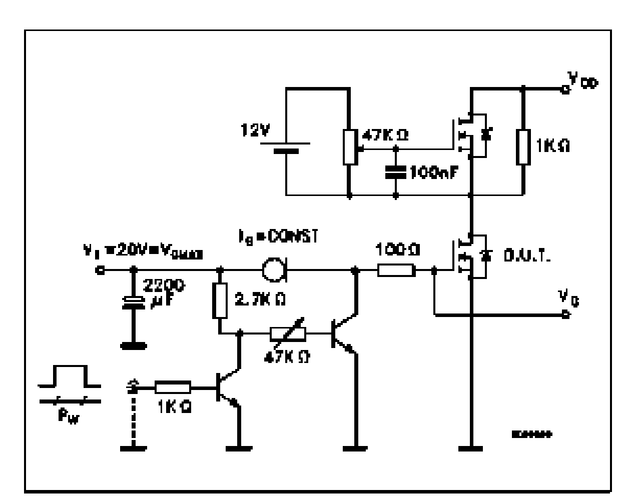
Unclamped Inductive Waveforms



Switching Time Test Circuit

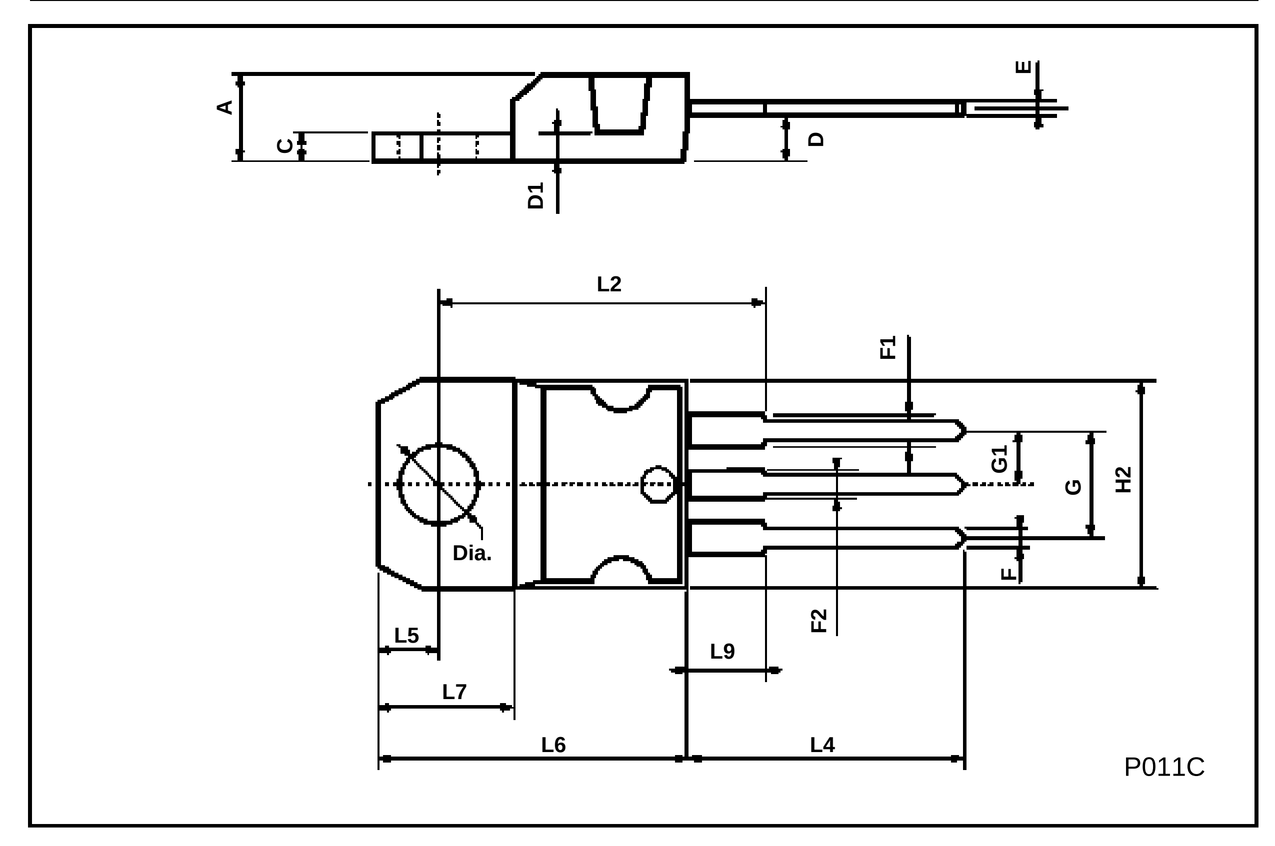


Gate Charge Test Circuit



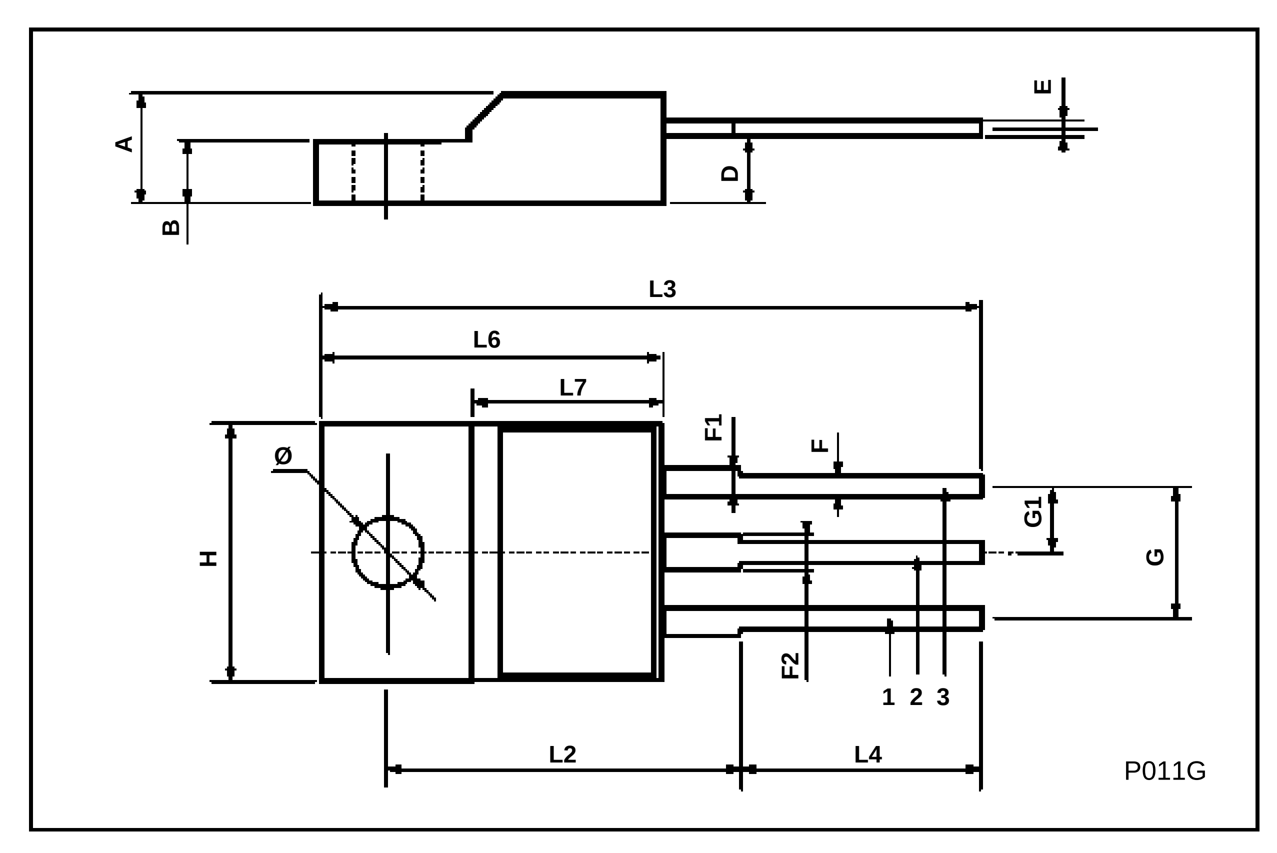
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



ISOWATT220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.4		0.7	0.015		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126




SGS-THOMSON
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